

Docket No.: 50090-306



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EACN
PATENT
4/10/03

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Hiroshi TOBIMATSU, et al.

Serial No.: 09/910,824

Group Art Unit: 2812

Filed: July 24, 2001

Examiner: LEE, Hsien Ming

For: METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE HAVING
PASSIVATION FILM AND BUFFER COATING FILM

AMENDMENT

Commissioner for Patents
Washington, DC 20231

Sir:

The following Amendment and Remarks are submitted in response to the Office
Action dated January 14, 2003.

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COMM. FOR PAT. & TRADEMARKS

IN THE CLAIMS:

Please amend claim 1 as follows.

1. (Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming an interconnection on a semiconductor substrate having a semiconductor element formed thereon;

forming a passivation film on the semiconductor substrate including the interconnection;